

- Drafts
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 - L1: (1923) optica and mesa and cladding
 - L2: (449) optical near device and mesa and cladding
 - L3: (1112) 1 and (indium near phosphide InP)
 - L4: (1) 1 and (indium near phosphide InP) and (phosphorous near trichloride PCl\$1)
 - L5: (1) 1 and (indium near phosphide) and (phosphorous near trichloride PCl\$1)
 - L6: (1) 1 and (indium near phosphide) and (phosphorous near trichloride)
 - L7: (221) 1 and (indium near phosphide)
 - L8: (1112) 1 and (indium near phosphide InP)
 - L9: (1608) optica and mesa and cladding near by
 - L10: (408) optica near device and mesa and cladding near by
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ପରିବହନ ଯୋଗାନ୍ତର ନାମ : ୦୯ ପରିବହନ ଯୋଗାନ୍ତର ନାମ :

ପ୍ରାଚୀର୍ଦ୍ଧ ପଦାର୍ଥ ଓ ପାତାଙ୍କ ବ୍ୟାପକ କ୍ଷେତ୍ରରେ ଯେତେବେଳେ

4	<input type="checkbox"/>	<input type="checkbox"/>	Document ID	Issue Date	Pages	Title	Current CR	Current XRef
100	<input type="checkbox"/>	<input type="checkbox"/>	US 2003006407 A1	20030109	17	Apparatus and a method of fabricating inverter channel devices with precision gate doping for a minimum interdigit spacing	257/12	257/164; 257/E29.25
101	<input type="checkbox"/>	<input type="checkbox"/>	US 20030062556 A1	20030102	12	Semiconductor laser device, a semiconductor laser array, and a method for aligning optical fibers with the source of the laser	372/50	372/46
102	<input type="checkbox"/>	<input type="checkbox"/>	US 20020167580 A1	20021212	34	Semiconductor optical device and the fabrication method	438/47	
103	<input type="checkbox"/>	<input type="checkbox"/>	US 20020187579 A1	20021212	18	METHOD FOR MANUFACTURING A SEMICONDUCTOR OPTICAL FUNCTIONAL DEVICE	438/43	438/38; 438/40
104	<input type="checkbox"/>	<input type="checkbox"/>	US 20020166736 A1	20021212	33	METHOD FOR FABRICATING SEMICONDUCTOR DEVICE AND SEMICONDUCTOR DEVICE	372/50	257/E21.108; 257/E21.119
105	<input type="checkbox"/>	<input type="checkbox"/>	US 20020179930 A1	20021205	40	Composite semiconductor structure and device with optical testing elements	257/190	
106	<input type="checkbox"/>	<input type="checkbox"/>	US 20020179929 A1	20021205	57	Semiconductor optical modulator, an optical amplifier and an integrated semiconductor light-emitting device	257/181	
107	<input type="checkbox"/>	<input type="checkbox"/>	US 20020175325 A1	20021128	14	Semiconductor optical devices	257/25	
108	<input type="checkbox"/>	<input type="checkbox"/>	US 20020163856 A1	20021114	11	Semi-insulating substrate, semiconductor optical device and fabrication method of semiconductor thin film	438/689	257/E33.027; 428/637; 428/542;
109	<input type="checkbox"/>	<input type="checkbox"/>	US 20020163948 A1	20021107	41	Semiconductor laser device having a diffraction grating on a light emission side	372/45	372/96
110	<input type="checkbox"/>	<input type="checkbox"/>	US 20020163688 A1	20021107	26	Optical communications system and vertical cavity surface emitting laser therefor	398/144	398/82; 398/91